

Vishay Siliconix

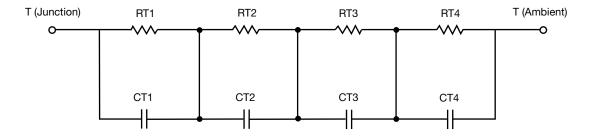
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK	-C VALUES FOR TANK CONFIGURATION					
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	182.8513	N/A	N/A			
RT2	53.3698	N/A	N/A			
RT3	293.2723	N/A	N/A			
RT4	116.3157	N/A	N/A			
	THERMAL CAPACIT	ANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	1.6618m	N/A	N/A			
CT2	161.6648u	N/A	N/A			
CT3	4.3408m	N/A	N/A			
CT4	126.7726m	N/A	N/A			

Note

• n/a indicates not applicable

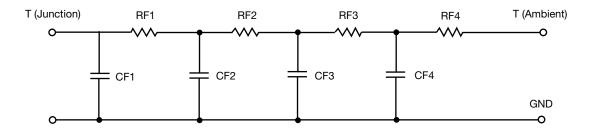
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	67.8843	N/A	N/A		
RF2	296.7408	N/A	N/A		
RF3	185.2792	N/A	N/A		
RF4	96.4249	N/A	N/A		
	THERMAL CAPACI	TANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	163.0989u	N/A	N/A		
CF2	1.0055m	N/A	N/A		
CF3	5.1616m	N/A	N/A		
CF4	143.6464m	N/A	N/A		

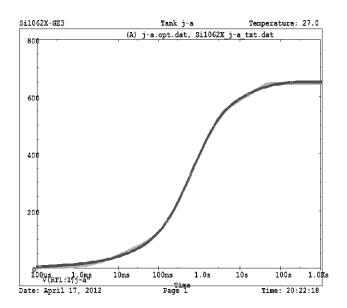
Note

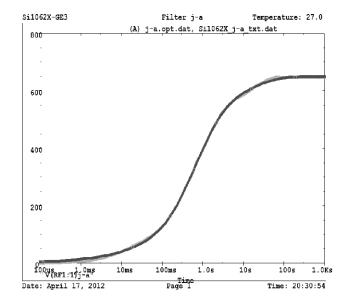
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Si1062X-GE3_RC

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